

CLEAN COPY OF AMENDED CLAIMS

15. (Amended) Passenger detector comprising
a flexible support made of an insulating fabric,
at least two electrode structures applied on said insulating fabric at a distance from each
other, each of said electrode structures comprising a lower surface and an opposing upper
surface, said lower surface being in contact with said insulating fabric, and
a layer of semiconducting material applied on top of said electrode structures in an active
zone of said detector, said layer of semiconducting material being arranged in intimate contact
with said upper surfaces of said electrode structures and having an internal resistance that varies
with a deformation of said layer.

18. (Amended) Passenger detector having a plurality of active zones, said detector
comprising a flexible support made of an insulating material,
at least two electrode structures applied on said flexible support at a distance from each
other, each of said electrode structures comprising a lower surface and an opposing upper
surface, said lower surface being in contact with said insulating material, and
a layer of semiconducting material, said layer of semiconducting material having an
internal resistance that varies with a deformation of said layer, said layer of semiconducting
material being divided into several zones, each of said zones being applied in one of said active
zones of said detector on said upper surfaces of said electrode structures and in intimate contact
with said electrode structures.

30. (Amended) Passenger detector having a plurality of active zones, said detector
comprising a flexible support made of an insulating fabric,

at least two electrode structures applied on said insulating fabric at a distance from each other, each of said electrode structures comprising a lower surface and an opposing upper surface, said lower surface being in contact with said insulating fabric, and

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a layer of semiconducting material, said layer of semiconducting material having an internal resistance that varies with a deformation of said layer, said layer of semiconducting material being divided into several zones, each of said zones being applied in one of said active zones of said detector on said upper surfaces of said electrode structures and in intimate contact with said electrode structures.